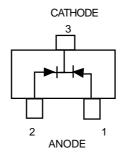


Common Anode Silicon Dual Switching diodes

These Common Cathode Silicon Epitaxial Planar Dual Diodes are designed for use in ultra high speed switching applications. These devices are housed in the SC-59 package which is designed for low power surface mount applications.

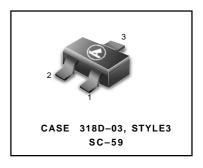
- Fast t rr, < 3.0 ns
- Low C_D , < 2.0 pF
- Available in 8 mm Tape and Reel
 Use M1MA151/2WKT1 to order the 7 inch/3000 unit reel.

 Use M1MA151/2WKT3 to order the 13 inch/10,000 unit reel.



M1MA151WKT1 M1MA152WKT1

SC-59 PACKAGE COMMON CATHODE DUAL SWITCHING DIODES 40/80 V-100mA SURFACE MOUNT



MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating		Symbol	Value	Unit
Reverse Voltage	M1MA151WAT1	V _R	40	Vdc
	M1MA152WAT1		80	
Peak Reverse Voltage	M1MA151WAT1 V RM		40	Vdc
	M1MA152WAT1		80	
Forward Current	Single	I _F	100	mAdc
	Dual		150	
Peak Forward Current	Single	I _{FM}	225	mAdc
	Dual		340	
Peak Forward Surge Current	Single	I _{FSM} ⁽¹⁾	500	mAdc
	Dual		750	

THERMAL CHARACTERISTICS

Rating	Symbo	lMax	Unit
Power Dissipation	P_D	200	mW
Junction Temperature	ΤJ	150	°C
Storage Temperature	T _{stg}	-55 to +150	℃

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic		Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Curre	ent M1MA151WAT1	I _R	V _R = 35 V		0.1	μAdc
	M1MA152WAT1		$V_R = 75 V$	_	0.1	
Forward Voltage		V _F	$I_F = 100 \text{ mA}$	_	1.2	Vdc
Reverse Breakdown Voltage	M1MA151WAT1	V _R	I _R = 100 μA	40		Vdc
	M1MA152WAT1			80	_	
Diode Capacitance		Съ	$V_R = 0, f = 1.0 \text{ MHz}$	_	2.0	pF
Reverse Recovery Time		t _{rr} (2)	$I_F = 10 \text{ mA}, V_R = 6.0 \text{ V},$	_	3.0	ns
			$R_L = 100\Omega, I_m = 0.1 I_R$			

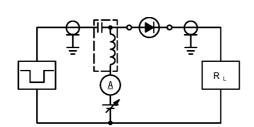
1. t = 1 SEC

2. t ... Test Circuit

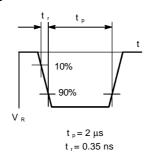


M1MA151WKT1 M1MA152WKT1

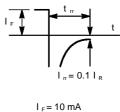
RECOVERY TIME EQUIVALENT TEST CIRCUIT



INPUT PULSE

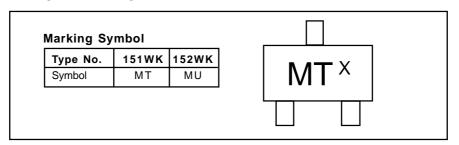






 $V_R = 6 V$ $R_L = 100 \Omega$

DEVICE MARKING—EXAMPLE



The "X" represents a smaller alpha digit Date Code. The Date Code indicates the actual month in which the part was manufactured.